DME20C01

Silicon PNP epitaxial planar type (Tr1) Silicon NPN epitaxial planar type (Tr2)

For general amplification

■ Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- ullet Low collector-emitter saturation voltage $V_{CE(sat)}$
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: A4

■ Basic Part Number

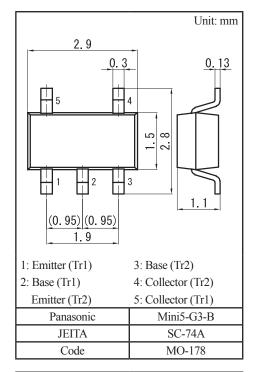
DSA2001 + DSC2001 (Base-emitterr connection)

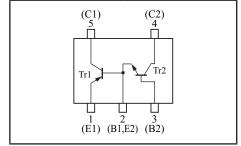
Packaging

 $DME20C010R \quad Embossed \ type \ (Thermo-compression \ sealing): \ 3\ 000\ pcs\ /\ reel \ (standard)$

\blacksquare Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter		Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	V _{CBO}	-60	V
	Collector-emitter voltage (Base open)	V _{CEO}	-50	V
	Emitter-base voltage (Collector open)	V_{EBO}	-7	V
	Collector current	I_{C}	-100	mA
	Peak collector current	I_{CP}	-200	mA
Tr2	Collector-base voltage (Emitter open)	V_{CBO}	60	V
	Collector-emitter voltage (Base open)	V _{CEO}	50	V
	Emitter-base voltage (Collector open)	$V_{\rm EBO}$	7	V
	Collector current	I_{C}	100	mA
	Peak collector current	I_{CP}	200	mA
Overall	Total power dissipation	P_{T}	300	mW
	Junction temperature	T_{j}	150	°C
	Operating ambient temperature	T _{opr}	-40 to +85	°C
	Storage temperature	T _{stg}	-55 to +150	°C





■ Electrical Characteristics $T_a = 25$ °C±3°C

• Tr1

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\rm C} = -10 \mu \text{A}, I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu A, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\rm CB} = -20 \text{ V}, I_{\rm E} = 0$			-0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -10 \text{ V}, I_{B} = 0$			-100	μΑ
Forward current transfer ratio	h_{FE}	$V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$	210		460	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		- 0.2	-0.5	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2		pF

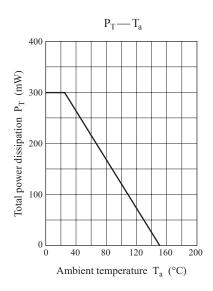
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• Tr2

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu A, I_E = 0$	60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu A, I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}, I_{B} = 0$			100	μΑ
Forward current transfer ratio	h_{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	210		460	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.5		pF

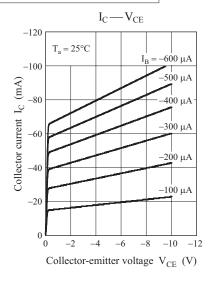
 $Note)\ Measuring\ methods\ are\ based\ on\ JAPANESE\ INDUSTRIAL\ STANDARD\ JIS\ C\ 7030\ measuring\ methods\ for\ transistors.$

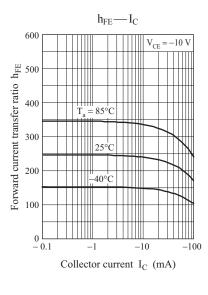
Common characteristics chart

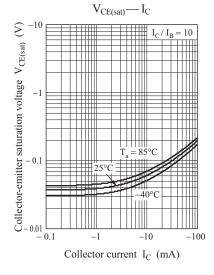


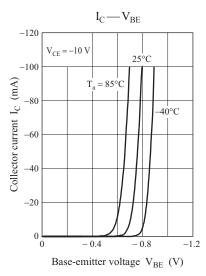
Ver. DED 2

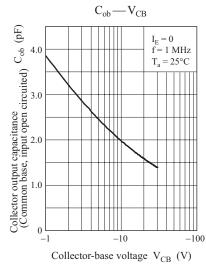
Characteristics charts of Tr1

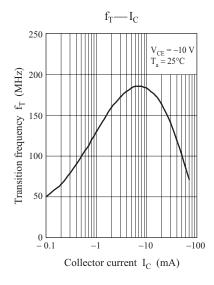




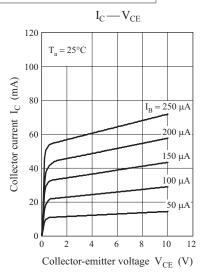


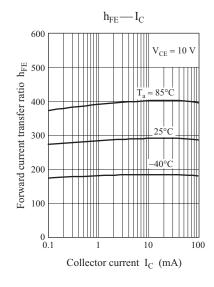


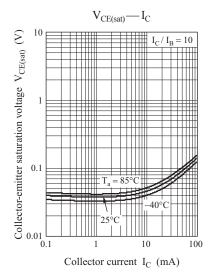




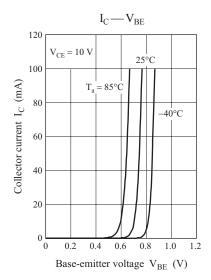
Characteristics charts of Tr2

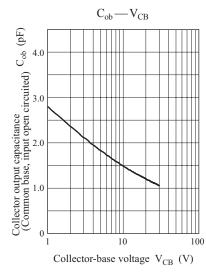


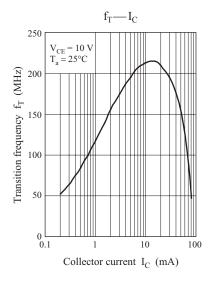




Ver. DED 3



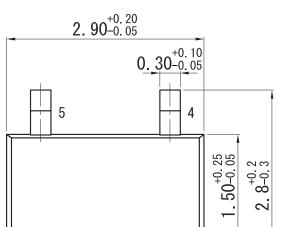




Ver. DED 4

Unit: mm

Mini5-G3-B



2

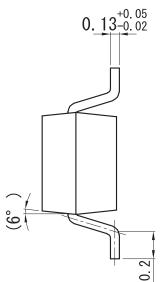
 1.9 ± 0.1

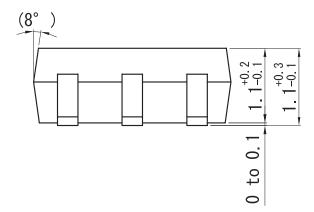
(0.95)

(0.95)

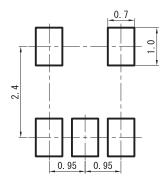
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(0.65)





■ Land Pattern (Reference) (Unit: mm)



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Customer Service :

Email service@ameya360.com

Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com